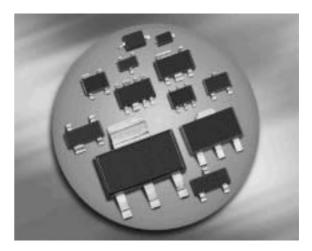


Silicon Low Leakage Diode Array

- Low-leakage applications
- Medium speed switching times
- Pb-free (RoHS compliant) package¹⁾
- Qualified according AEC Q101





BAV170



Туре	Package	Configuration	Marking
BAV170	SOT23	common cathode	JXs

Maximum Ratings at $T_A = 25^{\circ}$ C, unless otherwise specified

Parameter	Symbol	Value	Unit	
Diode reverse voltage	V _R	80	V	
Peak reverse voltage	V _{RM}	85		
Forward current	I _F	200	mA	
Non-repetitive peak surge forward current	I _{FSM}		A	
<i>t</i> = 1 μs		4.5		
<i>t</i> = 1 s		0.5		
Total power dissipation	Ptot	250	mW	
$T_{S} \leq 35^{\circ}C$				
Junction temperature	Tj	150	°C	
Storage temperature	T _{stg}	-65 150		

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ²⁾	R _{thJS}	≤ 460	K/W
BAV170			

¹Pb-containing package may be available upon special request

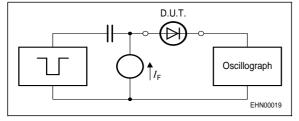
²For calculation of *R*_{thJA} please refer to Application Note Thermal Resistance



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics	1				1
Breakdown voltage	V _(BR)	85	-	-	V
<i>I</i> (BR) = 100 μA					
Reverse current	I _R				nA
V _R = 75 V		-	-	5	
$V_{\rm R} = 75 \text{ V}, \ T_{\rm A} = 150 \text{ °C}$		-	-	80	
Forward voltage	V _F				mV
<i>I</i> _F = 1 mA		-	-	900	
<i>I</i> _F = 10 mA		-	-	1000	
$I_{\rm F} = 50 \rm mA$		-	-	1100	
<i>I</i> _F = 150 mA		-	-	1250	
AC Characteristics					
Diode capacitance	CT	-	2	-	pF
$V_{\rm R} = 0 {\rm V}, f = 1 {\rm MHz}$					
Reverse recovery time	<i>t</i> _{rr}	-	0.6	1.5	μs
$I_{\rm F}$ = 10 mA, $I_{\rm R}$ = 10 mA, measured at $I_{\rm R}$ = 1mA,					
$R_{\rm L} = 100 \ \Omega$					

Electrical Characteristics at $T_A = 25^{\circ}$ C, unless otherwise specified

Test circuit for reverse recovery time



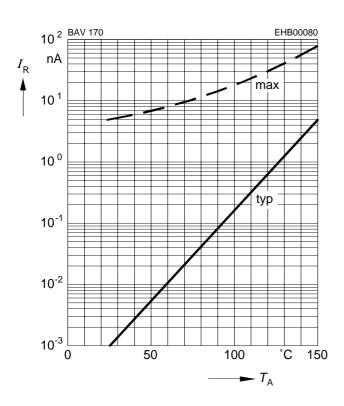
Pulse generator: $t_{\rm p}$ = 10µs, D = 0.05, $t_{\rm r}$ = 0.6ns, $R_{\rm i}$ = 50Ω

Oscillograph: $R = 50\Omega$, $t_r = 0.35$ ns, $C \le 1$ pF



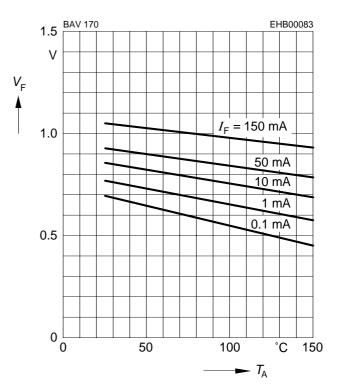
Reverse current $I_{R} = f(T_{A})$

 $V_{\mathsf{R}} = 70\mathsf{V}$



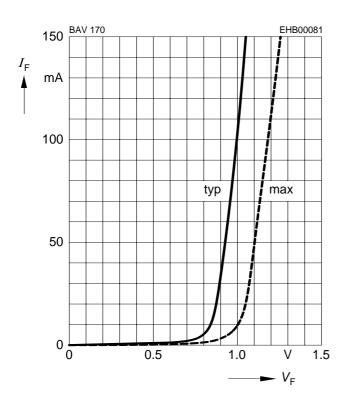
Forward Voltage $V_{\rm F} = f(T_{\rm A})$

 $I_{\rm F}$ = Parameter

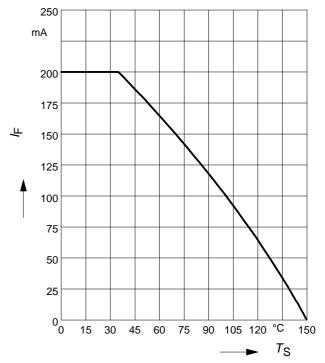


Forward current $I_{\rm F} = f (V_{\rm F})$

 $T_{\rm A} = 25^{\circ}{\rm C}$



Forward current $I_{\rm F} = f (T_{\rm S})$ BAV170

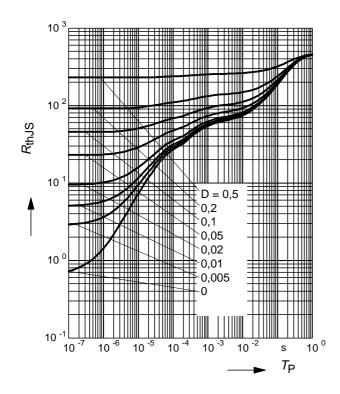


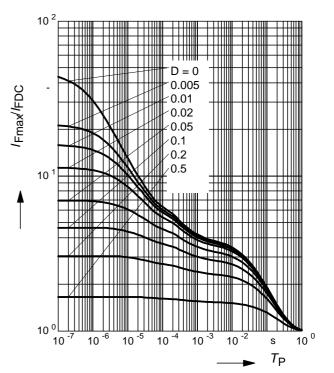


Permissible Puls Load $R_{thJS} = f(t_p)$

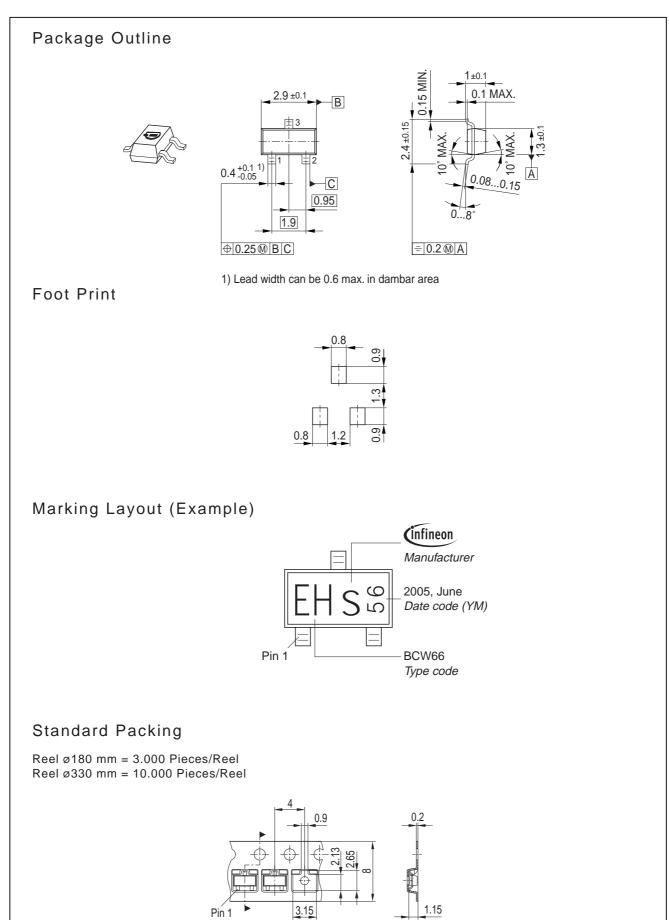
Permissible Pulse Load

 $I_{\text{Fmax}}/I_{\text{FDC}} = f(t_{\text{p}})$











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